

SILICON
TRANSISTORS

T0-92



ECB

2SB621, A (PNP) & 2SD592, A (NPN) are complementary silicon planar epitaxial transistors designed for AF output amplifiers.

ABSOLUTE MAXIMUM RATINGS

Collector-Base Voltage	VCBO	2SD592	2SD592A
Collector-Base Voltage	VCEO	2SB621	2SB621A
Collector-Base Voltage	VEBO	30V	60V
Collector-Base Voltage	VCEO	25V	50V
Collector-Base Voltage	VEBO		5V
Collector Current	IC		1A
Total Power Dissipation	Ptot		750mW
Operating Junction & Storage Temperature	Tj, Tstg		-55 to +150°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITION
Collector Cutoff Current	ICBO		100	nA	VCB=20V IE=0
Collector-Base Breakdown Voltage	BVCEO	30	60	V	IC=10µA IE=0
Collector-Base Breakdown Voltage	2SB621 / 2SD592	30			
Collector-Base Breakdown Voltage	2SB621A / 2SD592A	60			
Collector-Emitter Breakdown Voltage	LVCEO	25	50	V	IC=2mA IB=0
Collector-Emitter Breakdown Voltage	2SB621 / 2SD592	25			
Collector-Emitter Breakdown Voltage	2SB621A / 2SD592A	50			
Emitter-Base Breakdown Voltage	BVEBO	5		V	IE=10µA IC=0
D.C. Current Gain	HFE	85	340		IC=500mA VCE=10V*
D.C. Current Gain	HFE	50			IC=1A VCE=10V*
Collector-Emitter Saturation Voltage	VCE(sat)		0.4	V	IC=500mA IB=50mA*
Base-Emitter Saturation Voltage	VBE(sat)		1.2	V	IC=500mA IB=50mA*
Current Gain Bandwidth Product	fT	200 TYP		MHz	IC=50mA VCE=10V
Output Capacitance	Cob		30	pF	VCB=10V f=1MHz
Output Capacitance	2SB621, A		30	pF	
Output Capacitance	2SD592, A		20	pF	

Pulse Test : Pulse Width < 300µs, Duty Cycle < 1%.

HFE Grouping

Q : 85-170

R : 120-240

S : 170-340



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